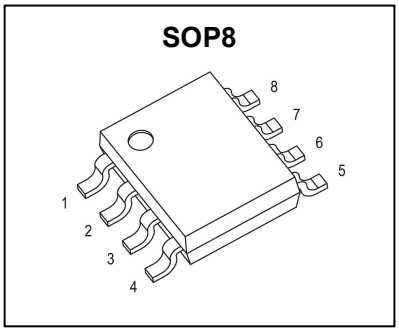
SOP8 Plastic-Encapsulate MOSFET

CJQ075SD10M6 Dual N-Channel MOSFET



Key Performance Parameters

$V_{BR(DSS)}$	$R_{DS(on)}$TYP	I_D
100V	48mΩ@10V	3.5A
	57mΩ@4.5V	

DESCRIPTION

The Dual N-Channel MOSFET uses SGT technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

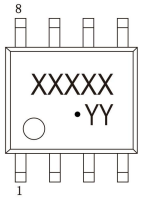
FEATURES

- Battery switch
- Load switch

APPLICATIONS

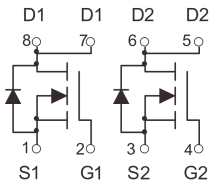
- SMPS and general purpose applications
- Hard switched and high frequency circuits
- Uninterruptible Power Supply

MARKING



XXXXX = 075SD10M6
Solid dot = Green molding compound device.
YY = Code.

EQUIVALENT CIRCUIT



ABSOLUTE MAXIMUM RATINGS (T_J=25℃ unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A =25℃	I_D⑥	3.5	A
	T_A =75℃		2.8	
Pulsed Drain Current		I_{DM}①②	14	A
Avalanche Current		I_{AS}③	5	A
Single Pulsed Avalanche Energy		E_{AS}③	6.25	mJ
Power Dissipation		P_D①⑥	1.8	W
Operating Junction and Storage Temperature Range		T_J,T_{stg}	-55~+150	℃

Thermal Characteristics

Parameter		Symbol	Value		Unit
			Typ	Max	
Thermal Resistance from Junction to Ambient	t≤10s	$R_{\theta JA}$⑥	50	70	℃/W
	Steady State		80	112	℃/W

Typical Characteristics

ELECTRICAL CHARACTERISTICS (T_J=25℃ unless otherwise specified)

Static Characteristics

Parameter	Symbol	Test Condition		Value			Unit
				Min	Typ	Max	
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA		100	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=100V,V_{GS}=0V	T_J=25℃	-	-	1.0	μA
			T_J=125℃	-	-	100	
Gate-body leakage current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V		-	-	±100	nA
Gate-threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA		1.0	1.6	3.0	V
Static drain-source on-sate resistance	$R_{DS(on)}$④	V_{GS}=10V, I_D=3A	T_J=25℃	-	48	75	mΩ
			T_J=125℃	-	82	128	
		V_{GS}=4.5V, I_D=3A		-	57	90	

Dynamic Characteristics⑤

Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=50V, f=1MHz	-	320	-	pF
Output capacitance	C_{oss}		-	60	-	
Reverse transfer capacitance	C_{rss}		-	4	-	
Total gate charge	Q_g	V_{GS}=4.5V, V_{DS}=50V, I_D=3A	-	3.4	-	nC
Total gate charge	Q_g	V_{GS}=10V, V_{DS}=50V, I_D=3A	-	6.3	-	nC
Gate charge at threshold	$Q_{G(th)}$		-	0.7	-	
Gate-source charge	Q_{gs}		-	0.9	-	
Gate-drain charge	Q_{gd}		-	1.6	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=50V, V_{GS}=10V, R_L=16.7Ω, R_g=6Ω	-	1.7	-	ns
Turn-on rise time	t_r		-	9.7	-	
Turn-off delay time	$t_{d(off)}$		-	25.2	-	
Turn-off fall time	t_f		-	67.9	-	

Reverse Diode Characteristics

Drain-source diode forward voltage	V_{SD}④	V_{GS}=0V, I_S=3A	-	-	1.2	V
Continuous drain-source diode forward current	I_S①		-	-	3.5	A
Pulsed drain-source diode forward current	I_{SM}①②		-	-	14	A
Reverse recovery time	t_{rr}	V_{DD}=20V, I_S=3A, di/dt=100A/μs	-	37	-	ns
Reverse recovery charge	Q_{rr}		-	16	-	nC

Notes:

①.Limited only by maximum temperature allowed.

②.P_W≤10μs, Duty cycle ≤1%.

③.EAS condition: V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_g=25Ω Starting T_J=25℃.

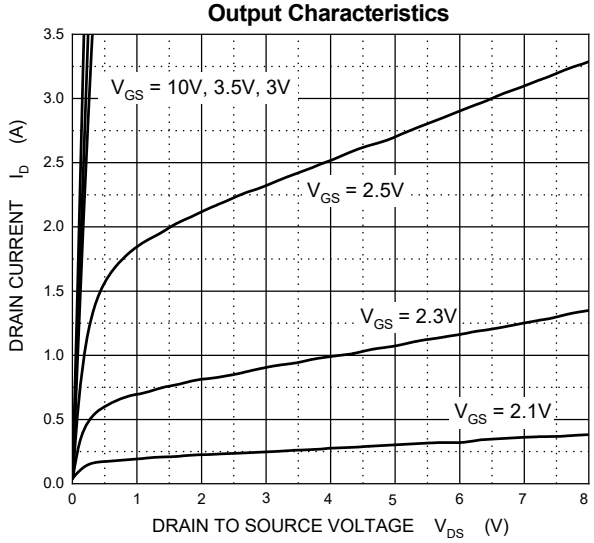
④.Pulse Test : Pulse Width ≤380μs, duty cycle ≤2%.

⑤.Guaranteed by design, not subject to production.

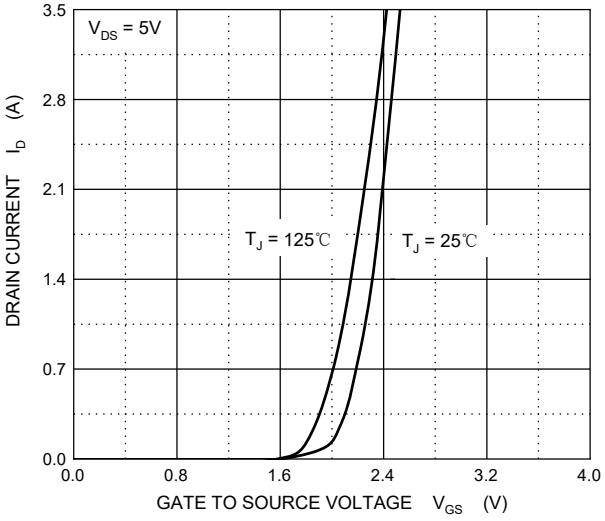
⑥.Device mounted on 1 in^2 FR-4 board with 2oz. double-sided Copper, in a still air environment with T_A=25℃. The current rating is based on the t ≤10s thermal resistance rating.

Typical Characteristics

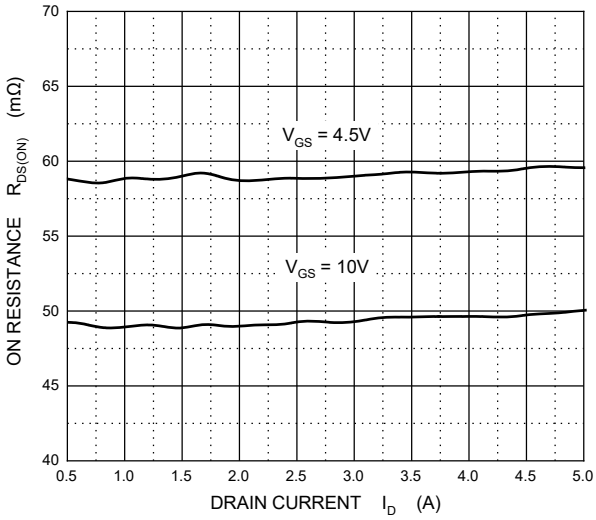
Output Characteristics



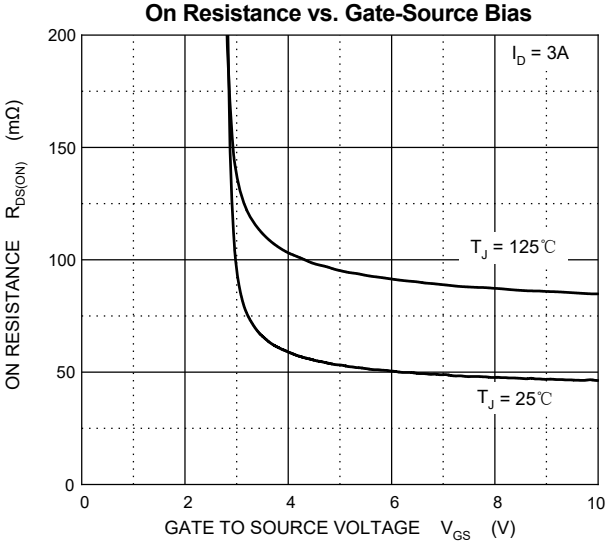
Transfer Characteristics



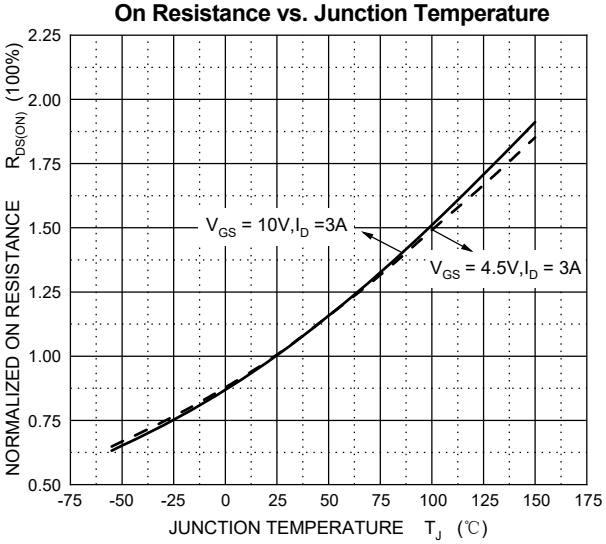
On Resistance vs. Drain Current



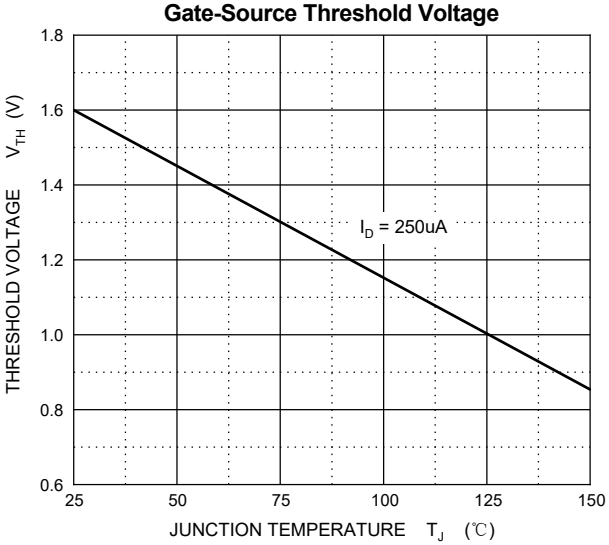
On Resistance vs. Gate-Source Bias



On Resistance vs. Junction Temperature

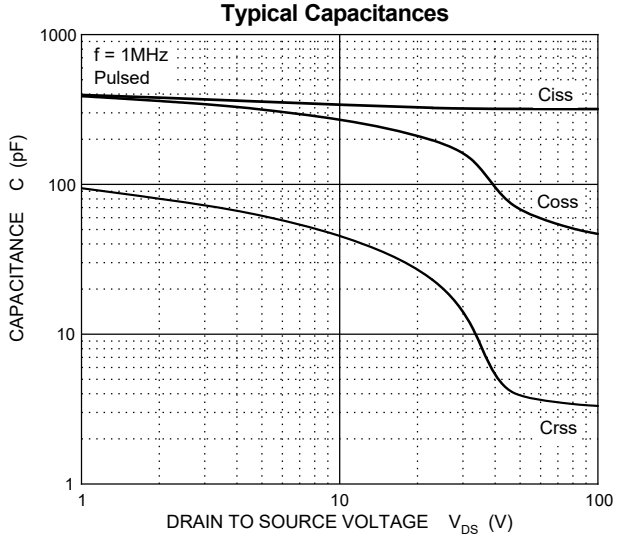


Gate-Source Threshold Voltage

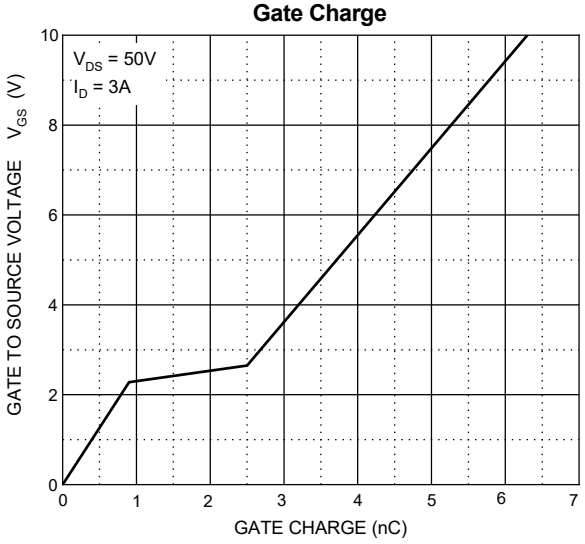


Typical Characteristics

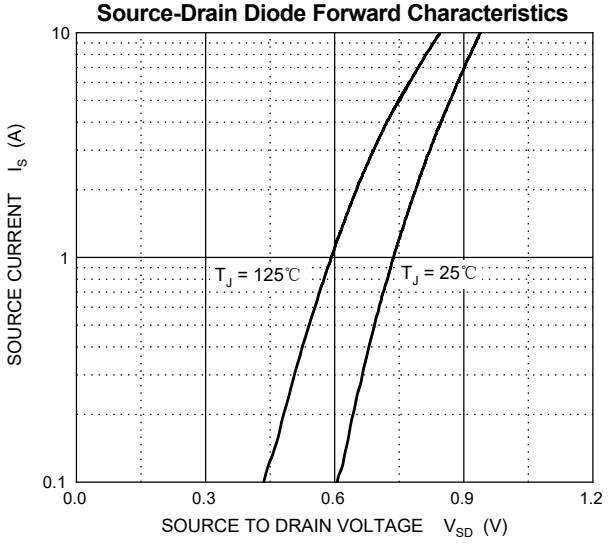
Typical Capacitances



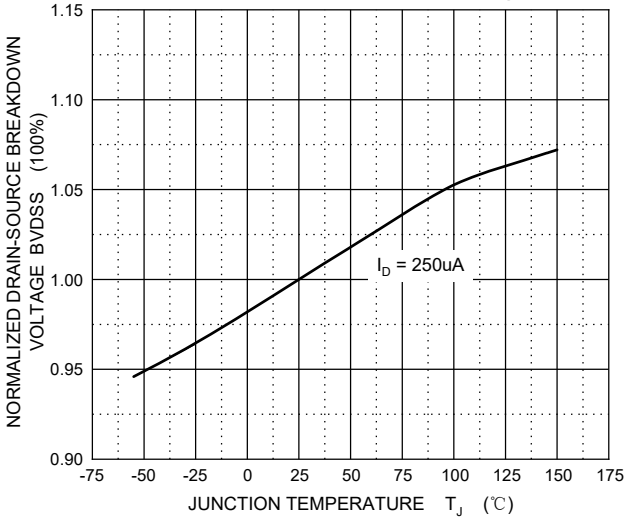
Gate Charge



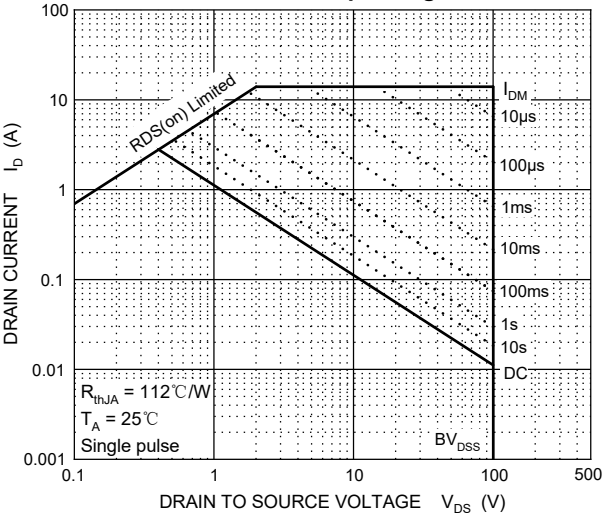
Source-Drain Diode Forward Characteristics



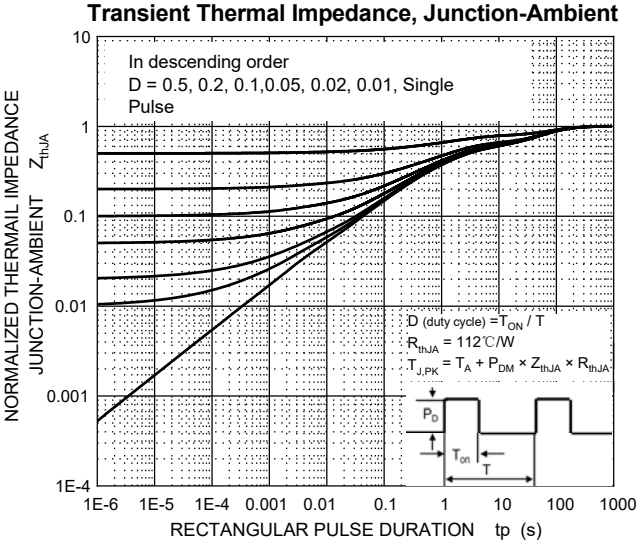
Drain-Source Breakdown Voltage



Maximum Safe Operating Area

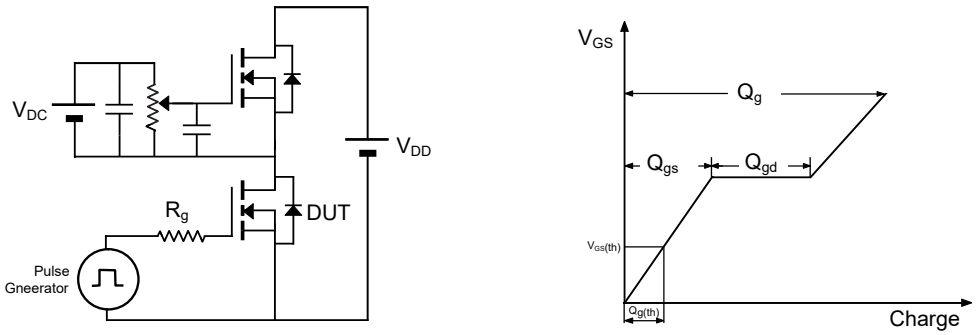


Transient Thermal Impedance, Junction-Ambient

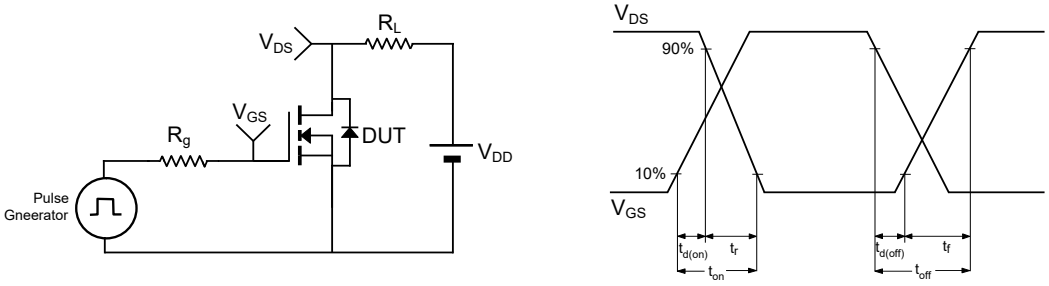


Test Circuit And Waveforms

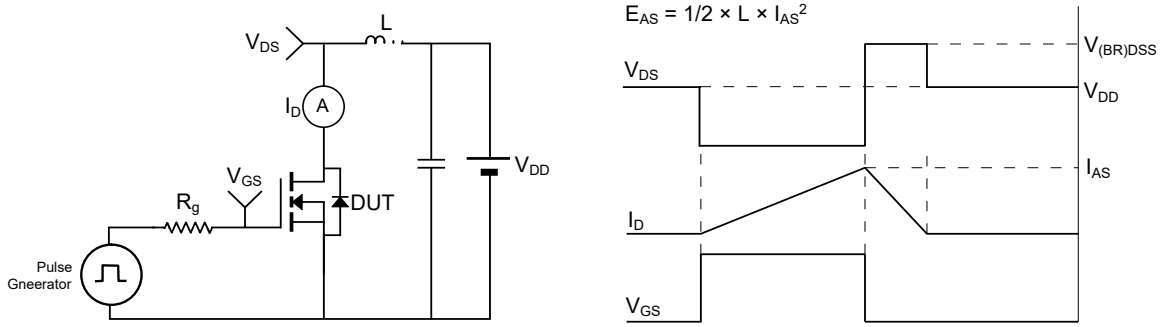
Gate Charge



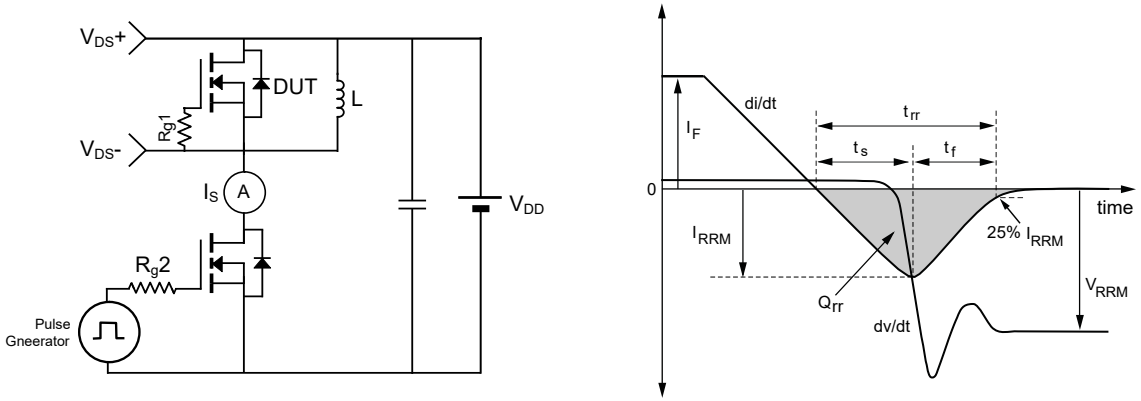
Resistive Load Switching Time



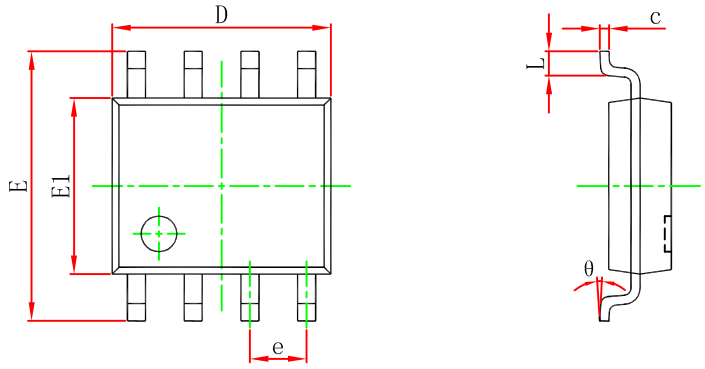
Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery

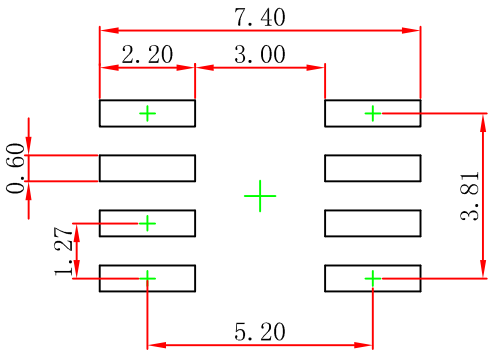


SOP8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	**Max**	**Min**	**Max**
A	1.450	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
e	1.270（BSC）		0.050（BSC）	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

SOP8 Suggested Pad Layout



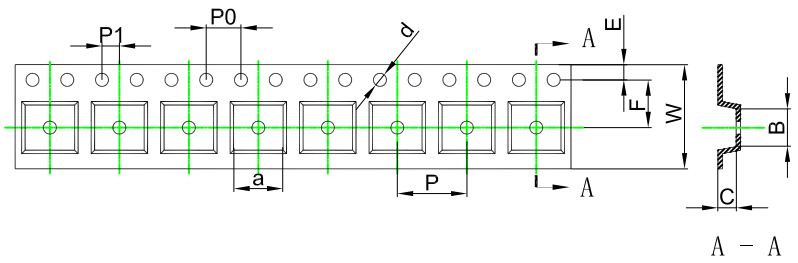
Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

NOTICE

SZCJ reserves the right to make modifications,enhan nts,improvements,corrections or other es without further notice to any product herein. SZCJ does not assume any liability arising out of the application or use of any product described h

SOP8 Tape and Reel

SOP8 Embossed Carrier Tape



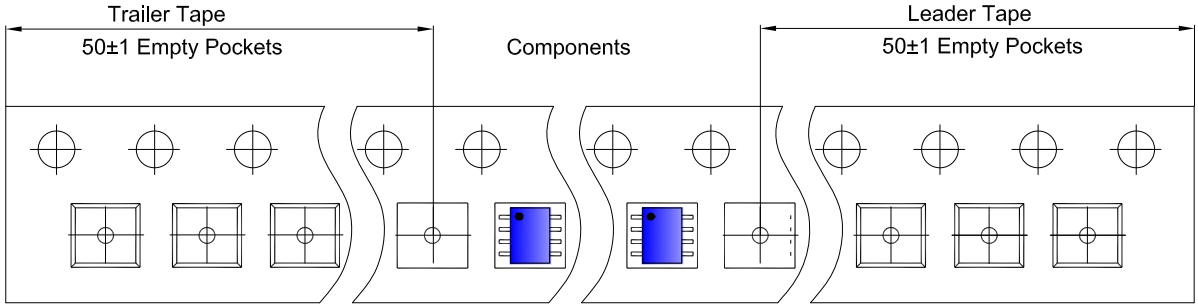
Packaging Description:

SOP8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 4000 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

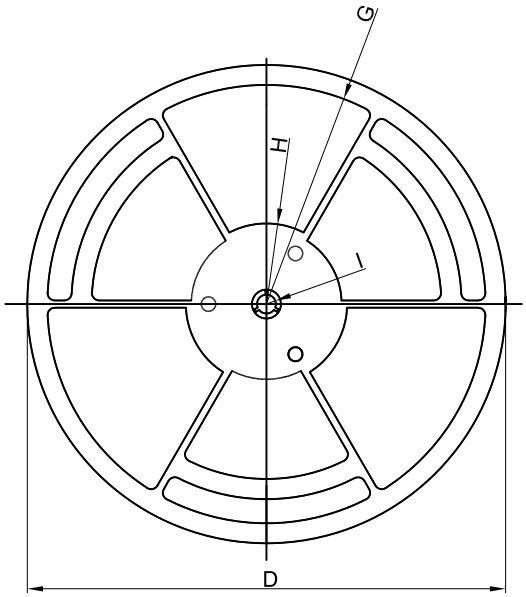
ALL DIM IN mm

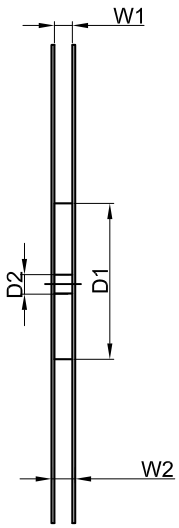
Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
SOP8	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

SOP8 Tape Leader and Trailer



SOP8 Reel





Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R151.00	R56.00	R6.50	12.40	17.60

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
4,000 pcs	13 inch	8,000 pcs	360×360×65	40,000 pcs	378×358×382	